



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Kie Y. Ahn et al.

Title: GATE OXIDES AND METHODS OF FORMING

Docket No.: 1303.021US1

Filed: August 30, 2001

Examiner: Walter Lindsay

Customer No.: 21186

Serial No.: 09/944,981

Due Date: October 14, 2004

Group Art Unit: 2812

Confirmation No.: 1912

Commissioner for Patents

Attn: MAIL STOP ISSUE FEE

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SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

Customer Number: 21186

By 

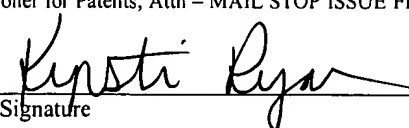
David C. Peterson

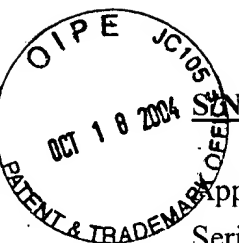
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Name


Signature



SN 09/944,981

PATENT

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Title: GATE OXIDES AND METHODS OF FORMING

COMMUNICATION CONCERNING RELATED APPLICATION(S)

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P.O. Box 1450
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Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
09/945535	August 30, 2001	1303.026US1	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO ₂
10/052983 6767795	January 17, 2002	1303.031US1	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrO _x Ny
10/027315	December 20, 2001	1303.033US1	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/081439	February 20, 2002	1303.046US1	EVAPORATED LaAlO ₃ FILMS FOR GATE DIELECTRICS
10/137499	May 2, 2002	1303.050US1	ATOMIC LAYER-DEPOSITED LaAlO ₃ FILMS FOR GATE DIELECTRICS
10/163481	June 5, 2002	1303.056US1	ATOMIC LAYER-DEPOSITED HfAlO ₃ FILMS FOR GATE DIELECTRICS
10/163686	June 5, 2002	1303.059US1	A METHOD INCLUDING FORMING GATE DIELECTRICS HAVING MULTIPLE LANTHANIDE OXIDE LAYERS
10/219870	August 15, 2002	1303.069US1	LANTHANIDE DOPED TiO _x DIELECTRIC FILMS BY PLASMA

OXIDATION

10/219878 6790791	August 15, 2002	1303.070US1	LANTHANIDE DOPED TiO _x DIELECTRIC FILMS
10/229903	August 28, 2002	1303.078US1	ATOMIC LAYER DEPOSITED HfSiON DIELECTRIC FILMS
10/233309	August 29, 2002	1303.079US1	ATOMIC LAYER DEPOSITED LANTHANIDE DOPED TiO _x DIELECTRIC FILMS
10/309583	December 4, 2002	1303.082US1	ATOMIC LAYER DEPOSITED ZR-SN- TI-O FILMS USING TiI ₄
10/309935	December 4, 2002	1303.083US1	ATOMIC LAYER DEPOSITED Zr-Sn- Ti-O FILMS
10/379470	March 4, 2003	1303.090US1	ATOMIC LAYER DEPOSITED DIELECTRIC LAYERS
10/403734	March 31, 2003	1303.092US1	ATOMIC LAYER DEPOSITED ZrAl _x O _y DIELECTRIC LAYERS
10/420307	April 22, 2003	1303.097US1	ATOMIC LAYER DEPOSITED ZrTiO ₄ FILMS
10/602323	June 24, 2003	1303.101US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS
10/602315	June 24, 2003	1303.107US1	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS
09/779959	February 9, 2001		
09/838335	April 20, 2001		
09/881408	June 13, 2001		
09/908767	July 18, 2001		

10/765619	January 27, 2004	1303.033US2	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/768597	January 30, 2004	1303.033US3	LOW-TEMPERATURE GROWN HIGH-QUALITY ULTRA-THIN PRASEODYMIUM GATE DIELECTRICS
10/789042	February 27, 2004	1303.050US2	ATOMIC LAYER-DEPOSITED LaAlO ₃ FILMS FOR GATE DIELECTRICS
10/789044	February 27, 2004	1303.070US2	LANTHANIDE DOPED TiO _x DIELECTRIC FILMS
10/863953	June 9, 2004	1303.031US2	HIGHLY RELIABLE AMORPHOUS HIGH-k GATE DIELECTRIC ZrO _x Ny
10/930138	August 31, 2004	1303.044US2	EVAPORATION OF Y-Si-O FILMS FOR MEDIUM-k DIELECTRICS
10/930184	August 31, 2004	1303.021US2	GATE OXIDES AND METHODS OF FORMING
10/930516	August 31, 2004	1303.078US2	ATOMIC LAYER DEPOSITED HfSiON DIELECTRIC FILMS
10/931341	August 31, 2004	1303.082US2	ATOMIC LAYER DEPOSITED ZR-SN-TI-O FILMS USING TiI ₄
10/930431	August 31, 2004	1303.056US2	ATOMIC LAYER-DEPOSITED HfAlO ₃ FILMS FOR GATE DIELECTRICS
10/931365	August 31, 2004	1303.059US2	Pr ₂ O ₃ -BASED La-oxide GATE DIELECTRICS
10/931364	August 31, 2004	1303.069US2	LANTHANIDE DOPED TiO _x DIELECTRIC FILMS BY PLASMA OXIDATION
10/931343	August 31, 2004	1303.101US2	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRIC LAYERS

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Page 4

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10/931340	August 31, 2004	1303.107US2	LANTHANIDE OXIDE / HAFNIUM OXIDE DIELECTRICS
10/931356	August 31, 2004	1303.026US2	HIGHLY RELIABLE AMORPHOUS HIGH-K GATE OXIDE ZrO2

Respectfully submitted,

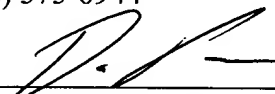
KIE Y. AHN ET AL.

By Applicants' Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 373-6944

Date 10-14-04

By



David C. Peterson

Reg. No. 47,857

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Kyrstih Ryan
Name

Kyrsti Ryan
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